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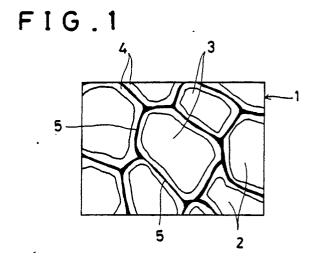
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Semiconductor ceramic of grain boundary insulation type.

There is disclosed a semiconductor ceramic of grain boundary insulation type comprising a polycrystalline substance. Each of grains (2) constituting said polycrystalline substance comprises a semiconductive oxide main phase (3) and a dielectric oxide composite phase (4) surrounding said main phase (3) and composed of a component of said main phase (3) and a component other than that of said main phase (3).



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EUROPEAN SEARCH REPORT

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X: particularly relevant if taken alone Y: particularly relevant if combined with another document of the same category A: technological background O: non-written disclosure P: intermediate document		E: earlier patent after the filin T: document cit L: document cit	T: theory or principle underlying the invention E: earlier patent document, but published on, or after the filing date D: document cited in the application L: document cited for other reasons &: member of the same patent family, corresponding document		